

TOSHIBA Field Effect Transistor Silicon N Channel MOS Type (L^2 - π -MOSV)

2SK2399

Chopper Regulator, DC-DC Converter and Motor Drive Applications

Unit: mm

- 4 V gate drive
- Low drain–source ON resistance : $R_{DS(ON)} = 0.17 \, \Omega$ (typ.)
- High forward transfer admittance : $|Y_{fs}| = 4.5 \, S$ (typ.)
- Low leakage current : $I_{DSS} = 100 \, \mu A$ (max) ($V_{DS} = 100 \, V$)
- Enhancement–mode : $V_{th} = 0.8 \sim 2.0 \, V$ ($V_{DS} = 10 \, V$, $I_D = 1 \, mA$)

Maximum Ratings (Ta = 25°C)

Characteristics		Symbol	Rating	Unit
Drain-source voltage		V_{DSS}	100	V
Drain-gate voltage ($R_{GS} = 20\text{ k}\Omega$)		V_{DGR}	100	V
Gate-source voltage		V_{GSS}	± 20	V
Drain current	DC (Note 1)	I_D	5	A
	Pulse (Note 1)	I_{DP}	20	A
Drain power dissipation ($T_c = 25^\circ\text{C}$)		P_D	20	W
Single pulse avalanche energy (Note 2)		E_{AS}	180	mJ
Avalanche current		I_{AR}	5	A
Repetitive avalanche energy (Note 3)		E_{AR}	2	mJ
Channel temperature		T_{ch}	150	$^\circ\text{C}$
Storage temperature range		T_{stg}	$-55\sim 150$	$^\circ\text{C}$

Thermal Characteristics

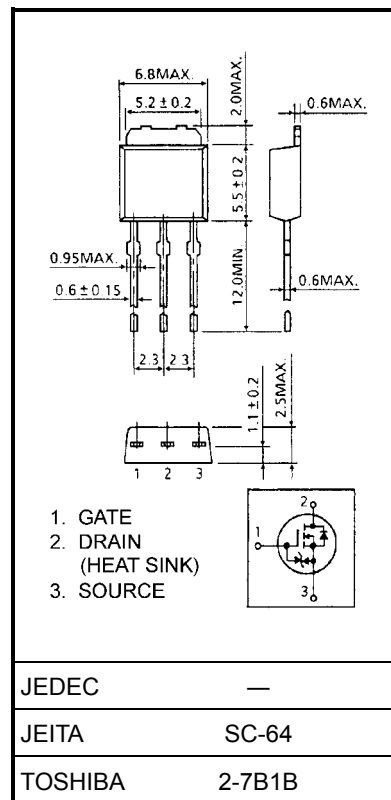
Characteristics	Symbol	Max	Unit
Thermal resistance, channel to case	$R_{th(ch-c)}$	6.25	$^{\circ}C / W$
Thermal resistance, channel to ambient	$R_{th(ch-a)}$	125	$^{\circ}C / W$

Note 1: Please use devices on condition that the channel temperature is below 150°C.

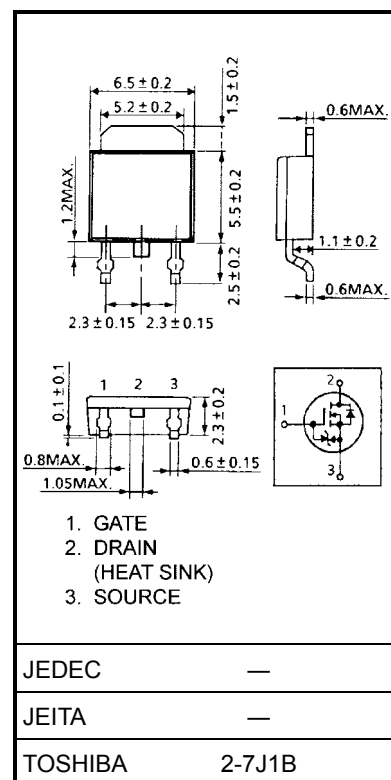
Note 2: $V_{DD} = 25\text{ V}$, $T_{ch} = 25^\circ\text{C}$ (initial), $L = 11.6\text{ mH}$, $R_G = 25\ \Omega$, $I_{AB} = 5\text{ A}$

Note 3: Repetitive rating: Pulse width limited by maximum channel temperature

This transistor is an electrostatic sensitive device.
Please handle with caution.

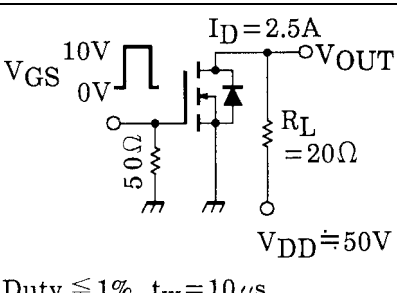


Weight: 0.36 g (typ.)



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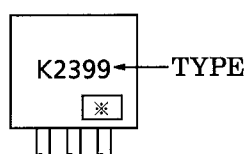
Electrical Characteristics (Ta = 25°C)

Characteristics		Symbol	Test Condition	Min	Typ.	Max	Unit
Gate leakage current		I_{GSS}	$V_{GS} = \pm 16 \text{ V}, V_{DS} = 0 \text{ V}$	—	—	± 10	μA
Drain cut-off current		I_{DSS}	$V_{DS} = 100 \text{ V}, V_{GS} = 0 \text{ V}$	—	—	100	μA
Drain-source breakdown voltage		$V_{(BR)DSS}$	$I_D = 10 \text{ mA}, V_{GS} = 0 \text{ V}$	100	—	—	V
Gate threshold voltage		V_{th}	$V_{DS} = 10 \text{ V}, I_D = 1 \text{ mA}$	0.8	—	2.0	V
Drain-source ON resistance		$R_{DS(ON)}$	$V_{GS} = 4 \text{ V}, I_D = 2.5 \text{ A}$	—	0.22	0.30	Ω
			$V_{GS} = 10 \text{ V}, I_D = 2.5 \text{ A}$	—	0.17	0.23	
Forward transfer admittance		$ Y_{fs} $	$V_{DS} = 10 \text{ V}, I_D = 2.5 \text{ A}$	2.0	4.5	—	S
Input capacitance		C_{iss}	$V_{DS} = 10 \text{ V}, V_{GS} = 0 \text{ V}, f = 1 \text{ MHz}$	—	500	—	pF
Reverse transfer capacitance		C_{rss}		—	80	—	
Output capacitance		C_{oss}		—	190	—	
Switching time	Rise time	t_r		—	17	—	ns
	Turn-on time	t_{on}		—	25	—	
	Fall time	t_f		—	50	—	
	Turn-off time	t_{off}		—	195	—	
Total gate charge (Gate-source plus gate-drain)		Q_g	$V_{DD} \approx 80 \text{ V}, V_{GS} = 10 \text{ V}, I_D = 5 \text{ A}$	—	22	—	nC
Gate-source charge		Q_{gs}		—	15	—	
Gate-drain ("miller") charge		Q_{gd}		—	7	—	

Source-Drain Ratings and Characteristics (Ta = 25°C)

Characteristics	Symbol	Test Condition	Min	Typ.	Max	Unit
Continuous drain reverse current (Note 1)	I_{DR}	—	—	—	5	A
Pulse drain reverse current (Note 1)	I_{DRP}	—	—	—	20	A
Forward voltage (diode)	V_{DSF}	$I_{DR} = 5 \text{ A}, V_{GS} = 0 \text{ V}$	—	—	-1.7	V
Reverse recovery time	t_{rr}	$I_{DR} = 5 \text{ A}, V_{GS} = 0 \text{ V}, dI_{DR} / dt = 50 \text{ A} / \mu\text{s}$	—	160	—	ns
Reverse recovery charge	Q_{rr}		—	0.28	—	μC

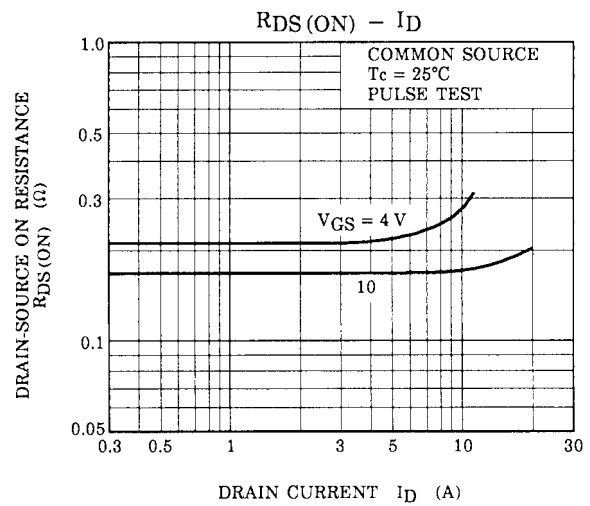
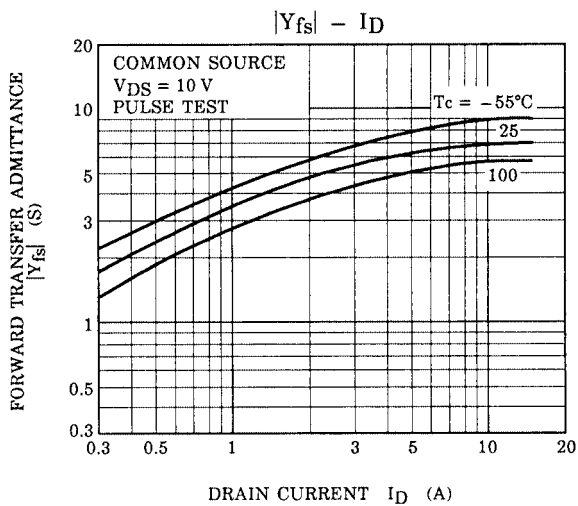
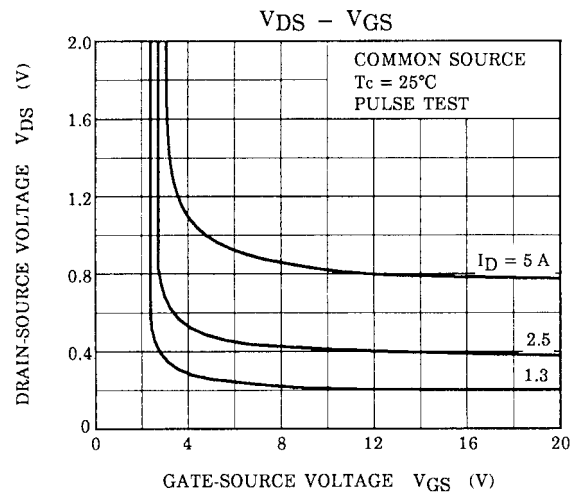
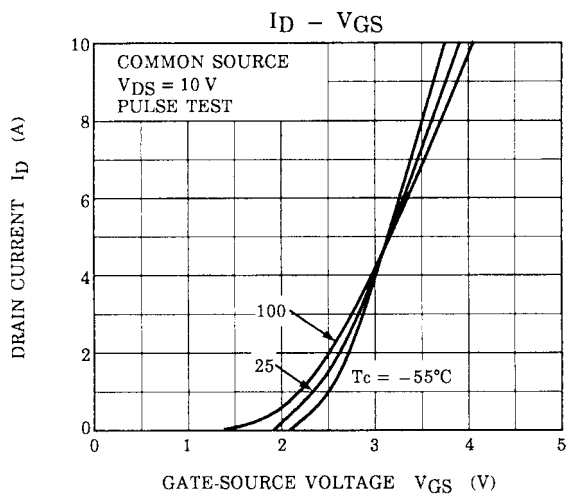
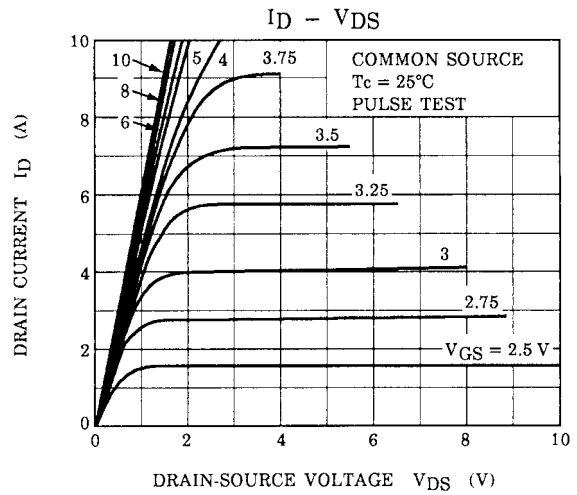
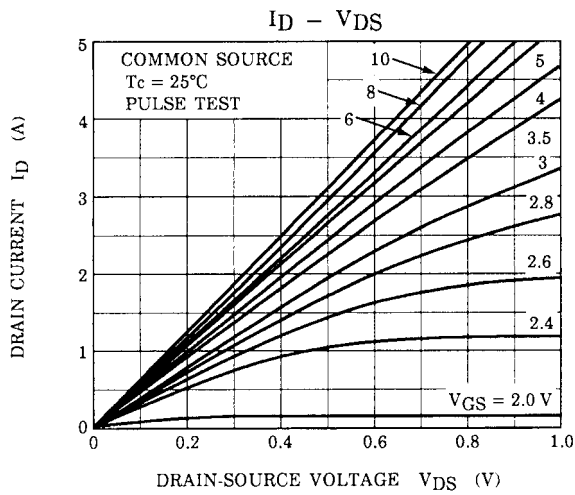
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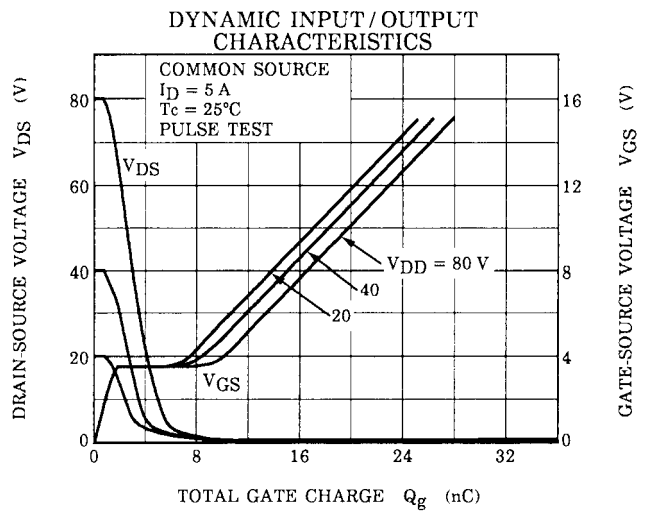
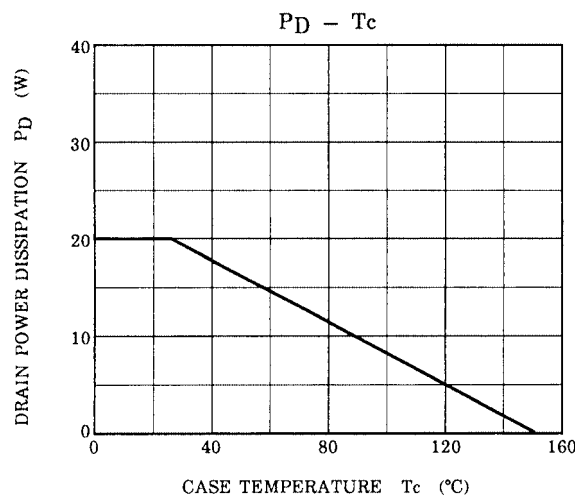
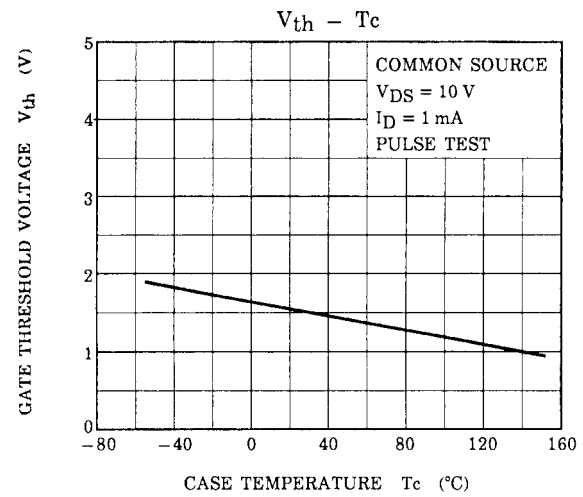
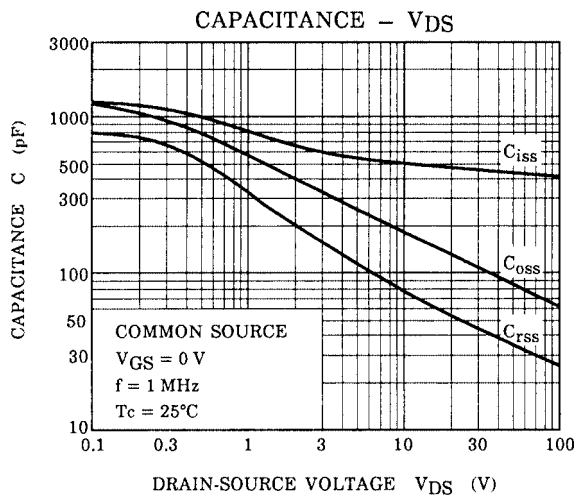
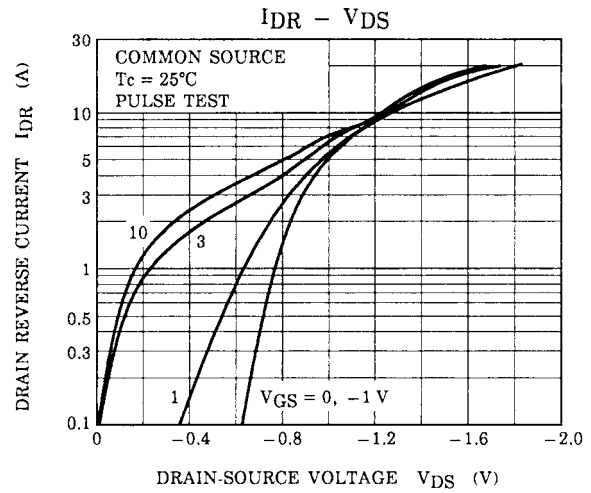
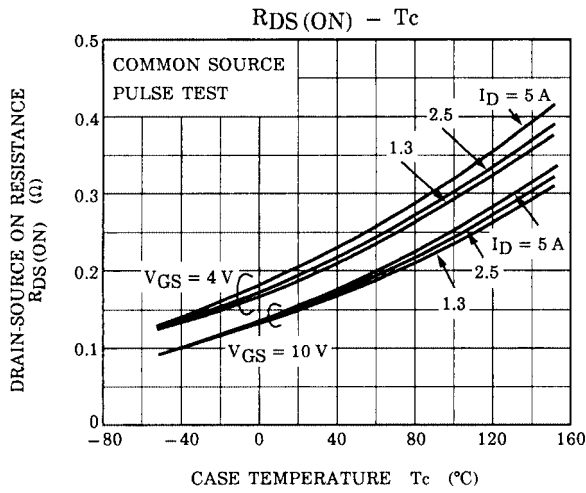


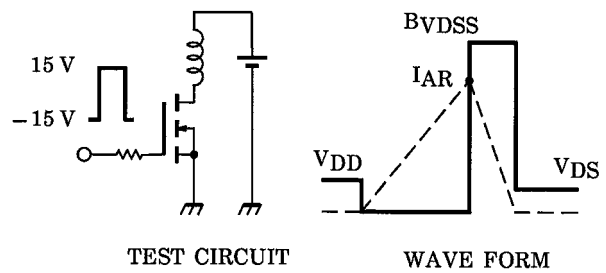
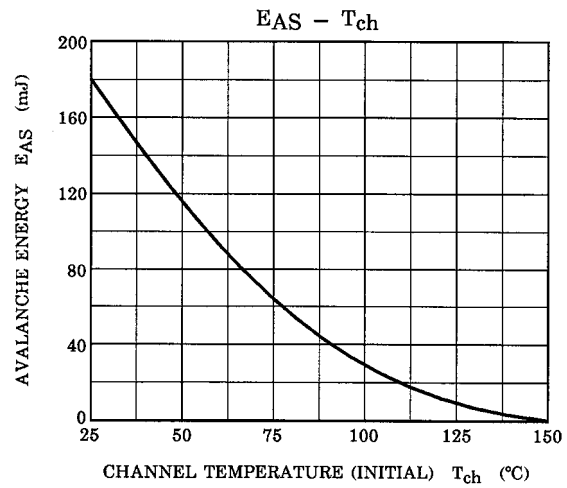
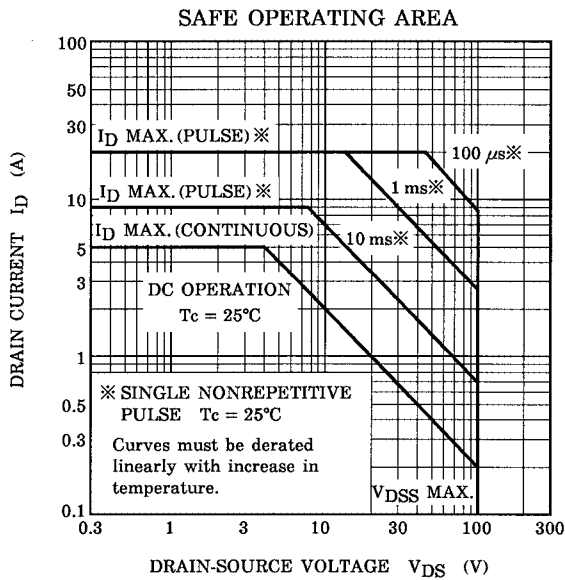
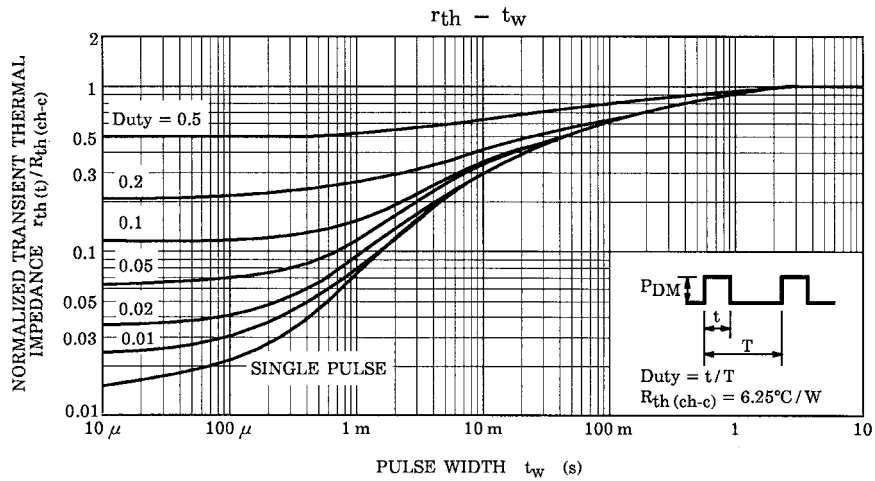
※ Lot Number

 Month (Starting from Alphabet A)

 Year (Last Number of the Christian Era)







$$R_G = 25 \, \Omega$$

$$V_{DD} = 25 \, \text{V}, L = 11.6 \, \text{mH}$$

$$E_{AS} = \frac{1}{2} \cdot L \cdot I^2 \cdot \left(\frac{B_{VDSS}}{B_{VDSS} - V_{DD}} \right)$$

RESTRICTIONS ON PRODUCT USE

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